



### 100V N-Channel Enhancement Mode MOSFET

Voltage

100 V

Current

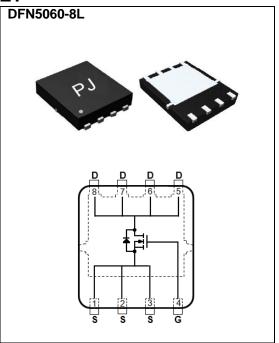
13A

#### **Features**

- RDS(ON), VGS@10V, ID@6.5A<115mΩ
- RDS(ON), VGS@4.5V, ID@4A<120mΩ
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

#### **Mechanical Data**

- Case: DFN5060-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0028 ounces, 0.08 grams
- Marking: Q5472A



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	100	V	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V	
Continuous Drain Current	T <sub>C</sub> =25°C	I <sub>D</sub>	13	А	
	T <sub>C</sub> =100°C		8		
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	52		
Power Dissipation	T <sub>C</sub> =25°C	Po	41	W	
	T <sub>C</sub> =100°C		16		
Continuous Drain Current	T <sub>A</sub> =25°C	I <sub>D</sub>	2.9	Α	
	T <sub>A</sub> =70°C		2.3	Α	
Power Dissipation	T <sub>A</sub> =25°C	Po	2.0	W	
	T <sub>A</sub> =70°C		1.3		
Single Pulse Avalanche Energy (Note 6)		E <sub>AS</sub>	6.1	mJ	
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	°C	
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	$R_{ heta JC}$	3.05	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





### **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =250uA	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	1.0	1.76	2.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V,I <sub>D</sub> =6.5A	-	92	115	mΩ
		V <sub>GS</sub> =4.5V,I <sub>D</sub> =4A	-	95	120	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1.0	uA
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Qg	V <sub>DS</sub> =50V, I <sub>D</sub> =2A, V <sub>GS</sub> =10V <sup>(Note 1,2)</sup>	-	20	-	nC
Gate-Source Charge	$Q_{gs}$		-	3.2	-	
Gate-Drain Charge	$Q_{gd}$		-	3.6	-	
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	1413	-	pF
Output Capacitance	Coss		-	60	-	
Reverse Transfer Capacitance	Crss	I=1.UIVINZ	-	34	-	
Turn-On Delay Time	td <sub>(on)</sub>	\/ F0\/   4A	-	18	-	
Turn-On Rise Time	t <sub>r</sub>	$V_{DD}$ =50V, $I_{D}$ =1A, $V_{GS}$ =10V, $R_{G}$ =3.3 $\Omega$ (Note 1,2)	-	4.3	-	ns
Turn-Off Delay Time	td <sub>(off)</sub>		-	41	-	
Turn-Off Fall Time	t <sub>f</sub>	K <sub>G</sub> =3.312	-	4.2	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	,				13	А
Diode Forward Current	I <sub>S</sub>		-	-	13	A
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A,V <sub>GS</sub> =0V	-	0.73	1	V

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. R<sub>OJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH,  $I_{AS}$ =11A,  $V_{DD}$ =25V,  $V_{GS}$ =10V
- 7. Guaranteed by design, not subject to production testing.





#### TYPICAL CHARACTERISTIC CURVES

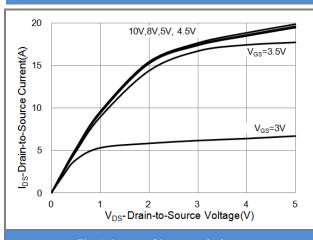
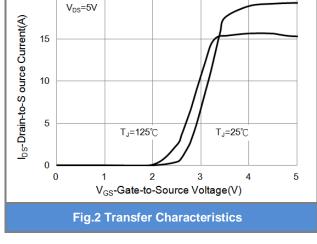


Fig.1 Output Characteristics



20

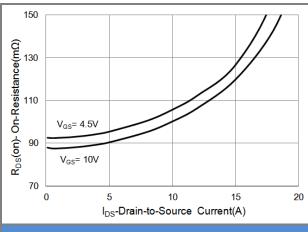


Fig.3 On-Resistance vs. Drain Current

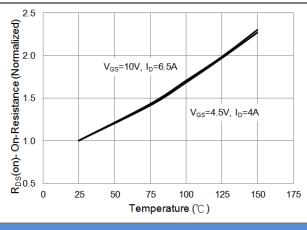
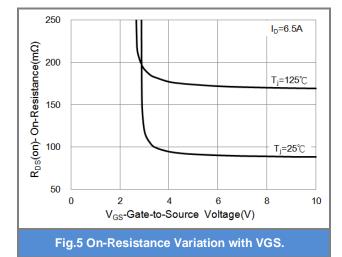


Fig.4 On-Resistance vs. Junction temperature



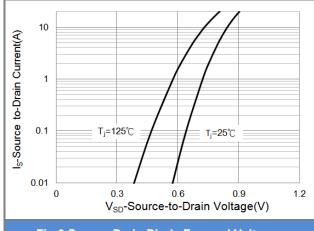
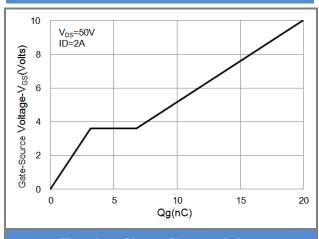


Fig.6 Source-Drain Diode Forward Voltage





#### TYPICAL CHARACTERISTIC CURVES



**Fig.7 Gate-Charge Characteristics** 

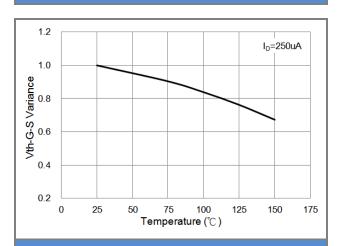
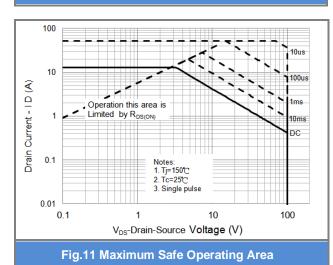


Fig.9 Threshold Voltage Variation with Temperature



1.1 I<sub>D</sub>=250uA I<sub>D</sub>=25

Fig.8 Breakdown Voltage Variation vs. Temperature

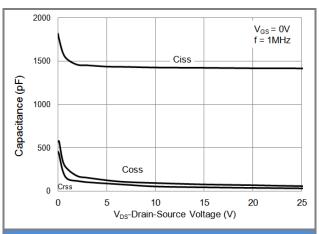


Fig.10 Capacitance vs. Drain-Source Voltage





#### **TYPICAL CHARACTERISTIC CURVES**

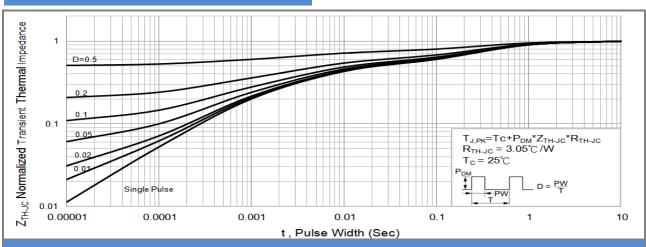


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

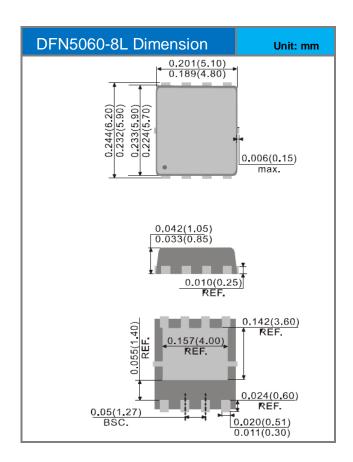


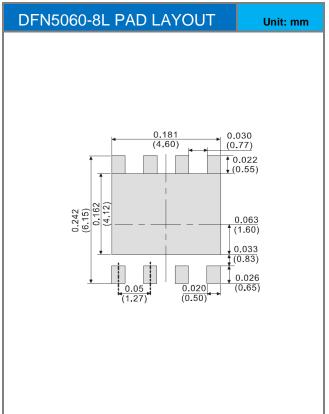


### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type Marking		Version	
PJQ5472A_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5472A	Halogen free	

### **Packaging Information & Mounting Pad Layout**









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